

1N4151W

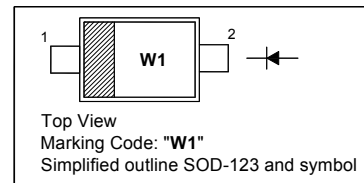
Silicon Epitaxial Planar Switching Diode

Features

- SOD-123 package
- Fast switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

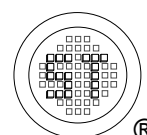


Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

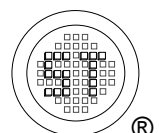
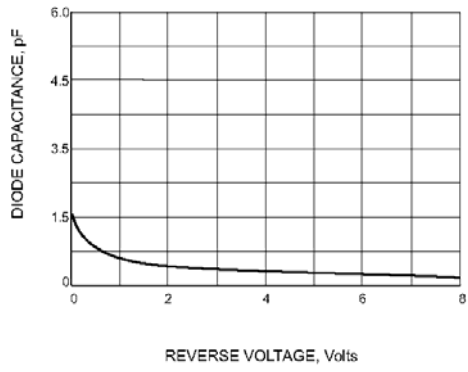
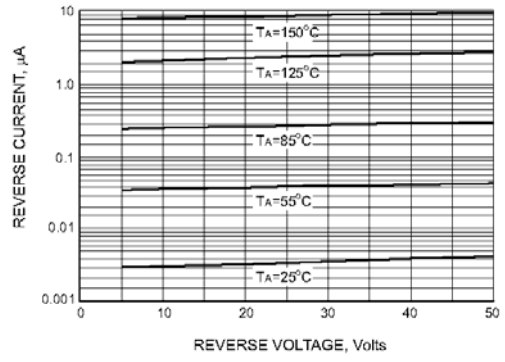
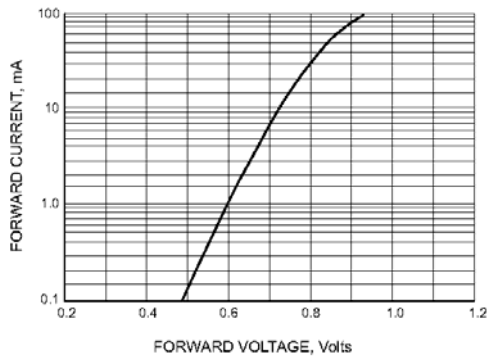
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	75	V
Reverse Voltage	V_R	50	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Non-repetitive Peak Forward Surge Current (at $t < 1\text{ s}$)	I_{FSM}	500	mA
Power Dissipation	P_{tot}	410	mW
Thermal Resistance from Junction to Ambient Air	$R_{\theta JA}$	305	$^\circ\text{C/W}$
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 50\text{ mA}$	V_F	-	1	V
Reverse Breakdown Voltage at $I_R = 5\text{ }\mu\text{A}$	$V_{(BR)R}$	75	-	V
Reverse Current at $V_R = 50\text{ V}$ at $V_R = 20\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$	I_R	-	50	nA μA
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	C_{tot}	-	2	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ through $I_R = 10\text{ mA}$ to $I_R = 1\text{ mA}$ at $I_F = 10\text{ mA}$ to $I_R = 1\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\text{ }\Omega$	t_{rr}	-	4 2	ns



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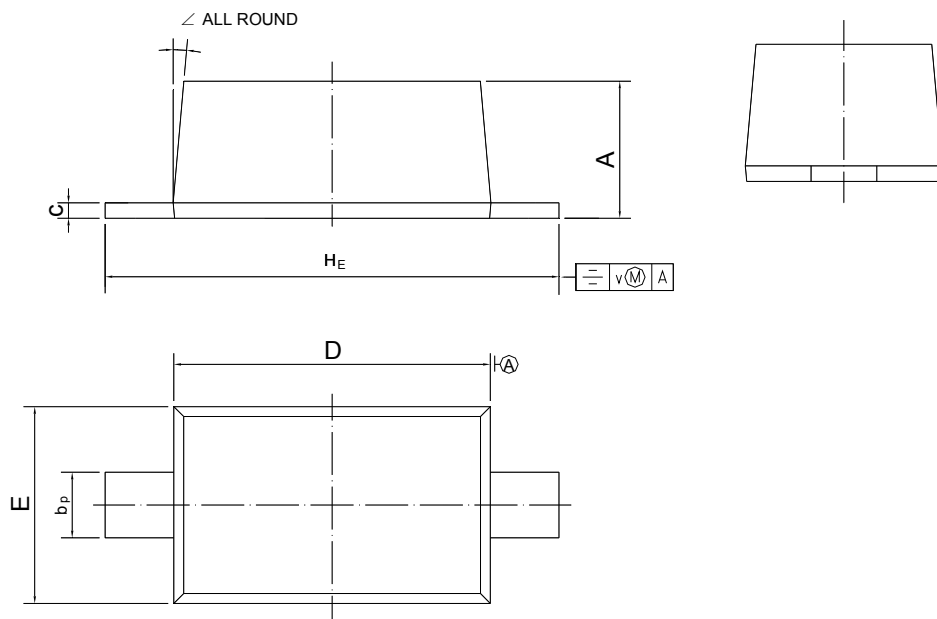


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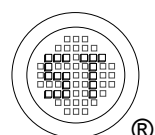
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b _p	c	D	E	H _E	v	∠
mm	1.15 1.05	0.6 0.5	0.135 0.100	2.7 2.6	1.65 1.55	3.85 3.55	0.2	5°



Dated : 15/06/2009